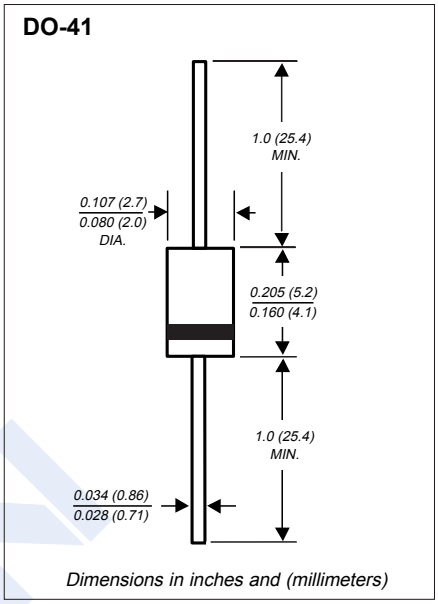
Schottky Diodes

SR120 ~ SR1100



■ Features

- Schottky Barrier Chip
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	SR120	SR130	SR140	SR150	SR160	SR180	SR1100	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	20	30	40	50	60	80	100	V
Working Peak Reverse Voltage	V_{RWM}								
Maximum DC Blocking Voltage	V_{DC}								
RMS Reverse Voltag	$V_{R(RMS)}$	14	21	28	35	42	56	70	
Forward Voltage	V_F	0.5			0.7		0.85		
Average Rectified Output Current @ T_L=100℃	I_O	1							A
Peak Forward Surge Current @ 8.3mS	I_{FSM}	40							
Maximum DC Reverse Current Ta=25℃	I_R	0.5							mA
Ta=100℃		10							
Typical Junction Capacitance (Note.1)	Cj	110			80				pF
Thermal Resistance.Junction- to-Ambient	R_{thJA}	50							℃/W
Thermal Resistance.Junction- to-Lead	R_{thJL}	15							
Junction Temperature	Tj	150							℃
Storage Temperature	Tstg	-65 to 150							

Note.1 Measured at 1MHz and applied reverse voltage of 4V D.C

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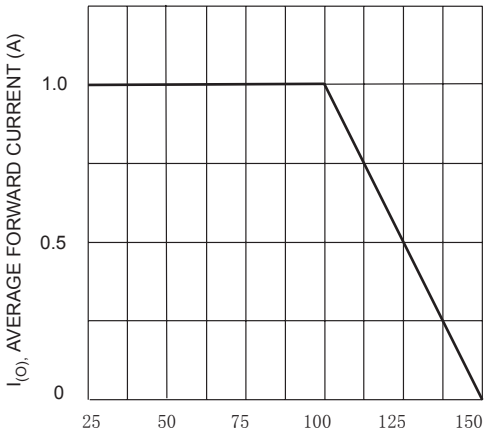
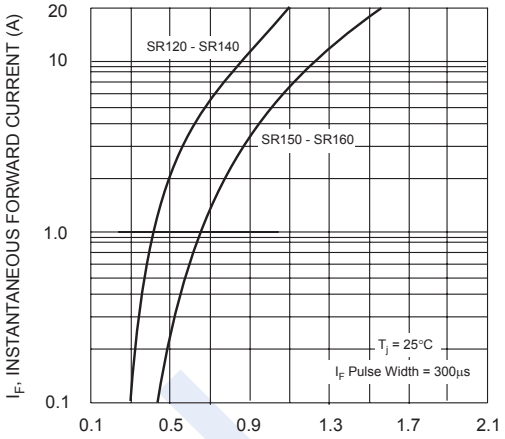
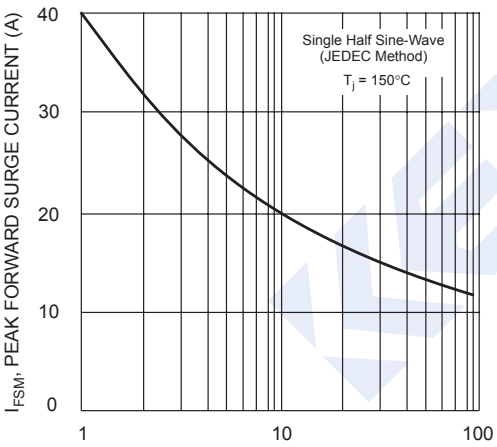
■ Typical Characterisitics



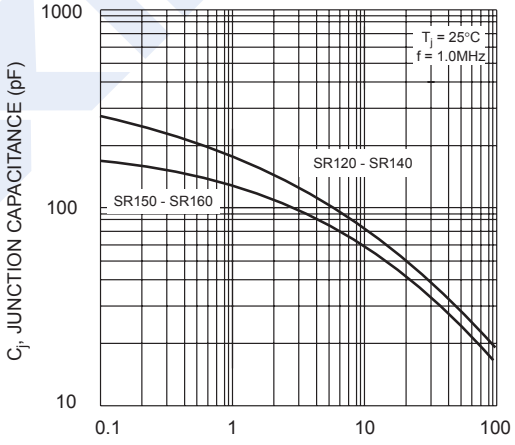
T_L, LEAD TEMPERATURE (°C)
Fig. 1 Forward Current Derating Curve



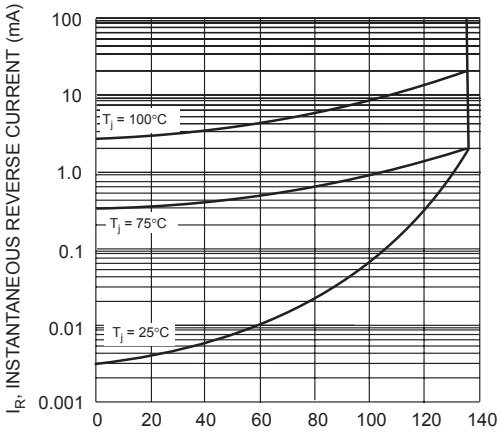
V_F, INSTANTANEOUS FORWARD VOLTAGE (V)
Fig. 2 Typical Forward Characteristics



NUMBER OF CYCLES AT 60 Hz
Fig. 3 Max Non-Repetitive Peak Fwd Surge Current



V_R, REVERSE VOLTAGE (V)
Fig. 4 Typical Junction Capacitance



PERCENT OF RATED PEAK REVERSE VOLTAGE (%)
Fig. 5 Typical Reverse Characteristics